

HIGH POWER NPN SILICON TRANSISTORS

The 2N6259 is power base power transistors designed for high power audio, disk head positioners, linear amplifiers, switching regulators, solenoid drivers, and dc to dc converters or inverters.

FEATURES:

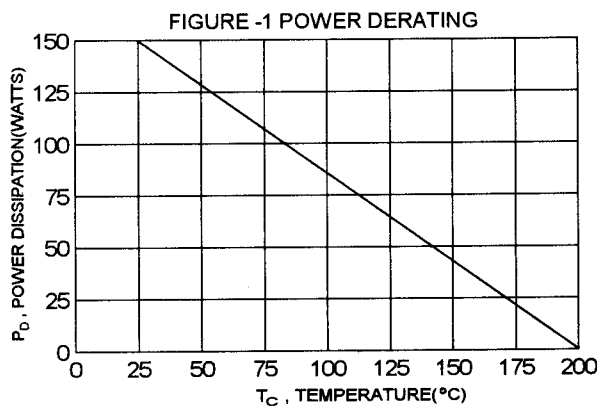
- * High Power Dissipation
 $P_D = 150 \text{ W}$ ($T_C = 25^\circ\text{C}$)
- * High DC Current Gain and Low Saturation Voltage
 $h_{FE} = 15-60$ @ $I_C = 8 \text{ A}$, $V_{CE} = 2 \text{ V}$
 $V_{CE(SAT)} = 1.0 \text{ V (Max.)}$ @ $I_C = 8 \text{ A}$, $I_B = 0.8 \text{ A}$

MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO(SUS)}$	150	V
Collector-Emitter Voltage	V_{CEX}	170	V
Collector-Base Voltage	V_{CBO}	170	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current-Continuous Peak (1)	I_C I_{CM}	16 30	A
Base Current-Continuous Peak (1)	I_B I_{BM}	4.0 15	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	150 0.857	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +200	$^\circ\text{C}$

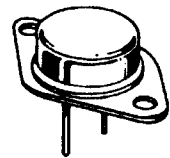
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.17	$^\circ\text{C/W}$

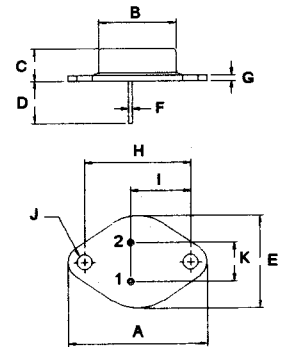


NPN
2N6259

16 AMPERE
POWER TRANSISTORS
NPN SILICON
150 VOLTS
150 WATTS



TO-3



PIN 1. BASE
2. EMITTER
COLLECTOR (CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

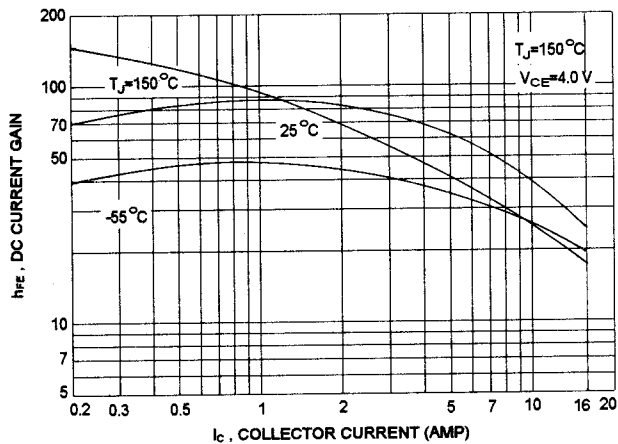
Collector - Emitter Sustaining Voltage (1) ($I_C = 100\text{ mA}$, $I_B = 0$)	$V_{CE(SUS)}$	150		V
Collector Cutoff Current ($V_{CE} = 130\text{ V}$, $I_B = 0$)	I_{CEO}		10	mA
Collector Cutoff Current ($V_{CE} = 150\text{ V}$, $V_{BE(OFF)} = 1.5\text{ V}$)	I_{CEX}		2.0	mA
Collector Cutoff Current ($V_{CB} = 150\text{ V}$, $I_E = 0$)	I_{CBO}		2.0	mA
Emitter Cutoff Current ($V_{EB} = 7.0\text{ V}$, $I_C = 0$)	I_{EBO}		5.0	mA

ON CHARACTERISTICS (1)

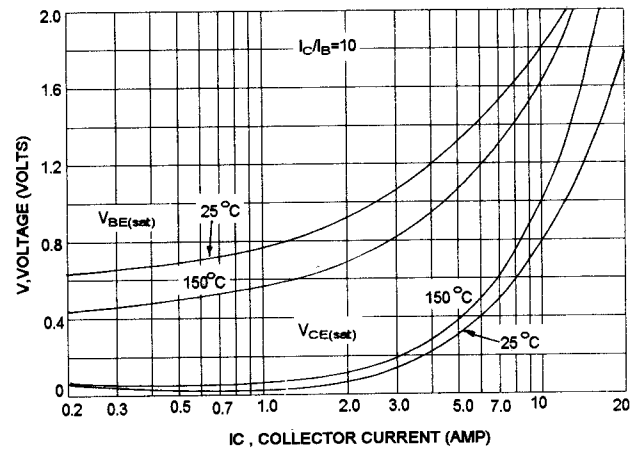
DC Current Gain ($I_C = 8.0\text{ A}$, $V_{CE} = 2.0\text{ V}$) ($I_C = 16\text{ A}$, $V_{CE} = 4.0\text{ V}$)	h_{FE}	15 10	60	
Collector - Emitter Saturation Voltage ($I_C = 8.0\text{ A}$, $I_B = 800\text{ mA}$) ($I_C = 16\text{ A}$, $I_B = 3.2\text{ A}$)	$V_{CE(sat)}$		1.0 2.5	V
Base - Emitter On Voltage ($I_C = 8.0\text{ A}$, $V_{CE} = 2.0\text{ V}$)	$V_{BE(ON)}$		2.0	V

(1) Pulse Test: Pulse width = 300 μs , Duty Cycle = 2.0%

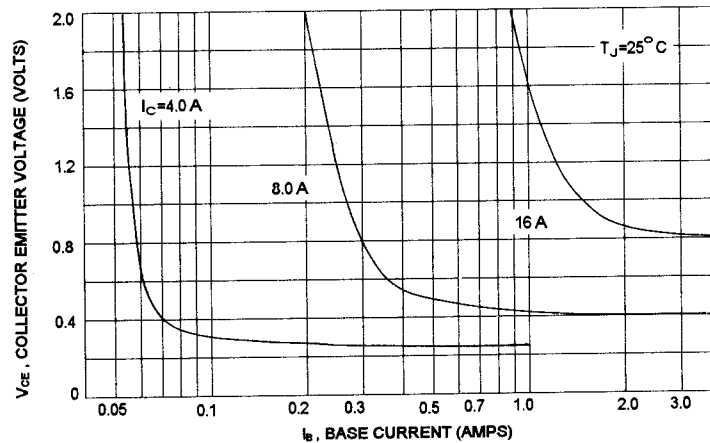
DC CURRENT GAIN



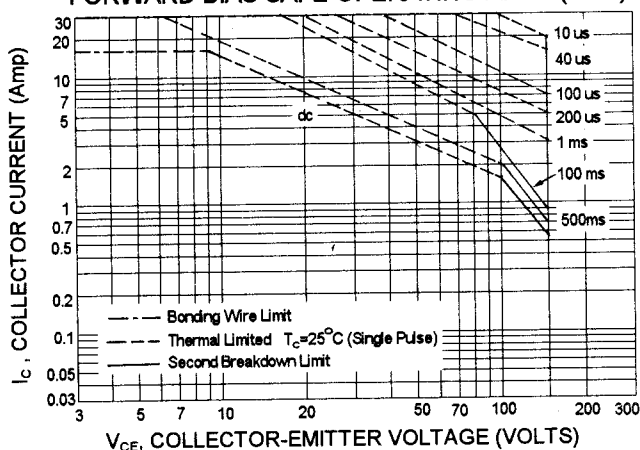
"ON" VOLTAGES



COLLECTOR SATURATION REGION



FORWARD BIAS SAFE OPERATING AREA (SOA)



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)} = 200^\circ\text{C}$; T_C is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 200^\circ\text{C}$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.